

**IN THE SPECIFICATION:**

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~striketrough~~.

Please REPLACE the paragraph [0018] with the following paragraph:

Fig. 1A is a schematic side view of an ion implanter 10. The implanter may be an Axcelis GSD™ platform implanter. The implanter has a chamber 105, which is kept at a very low pressure by cryo pumps, one of which is represented by reference numeral 115. Within the chamber 105, a beam gun 125 produces an ion beam 120 which is focused on wafers 210. The wafers 210 are placed around a disk 200. A faraday 100 is provided under the disk 200 to sense beam current. A first pressure sensor 135 is provided outside of the chamber 105 in the vicinity of the cryo pump 115. This location corresponds with a conventional location and is useful for implanting ions that produce a large pressure response during resist outgassing. A second pressure sensor 145 is provided within the chamber 105. The second pressure sensor (an ion gauge) 145 is useful for the implanting impurities that exhibit a smaller pressure response with resist outgassing. Both the first and second pressure sensors 135, 145 are connected to a pressure sensor controller 155. The pressure sensor controller 155 is in turn connected to a user interface 165. On the user interface 165, the pressure from one of the pressure sensors 135, 145 is displayed together with an indication of which pressure sensor or gauge is being used.